

INFORMATION DISCLOSURE CITATION

Atty. Docket No.	04173.0448	Application No.	10/823,541
Applicants	Hiroki SAKURAI et al.		
Filing Date	April 14, 2004	Group:	3729

U.S. PATENT DOCUMENTS							
Examiner Initial*		Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS						
	Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
<u>IN</u>	2003-234325	08/22/03	JAPAN			ABSTRACT
<u>IN</u>	2003-282734	10/03/03	JAPAN			ABSTRACT

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
<u>IN</u>	LEE, J. H. et al., "Mass Production Worthy HfO ₂ -Al ₂ O ₃ Laminate Capacitor Technology Using Hf Liquid Precursor for Sub-100nm DRAMs", IEEE, 4 pages, (2002).
<u>IN</u>	GUTSCHE, M. et al., "Capacitance Enhancement Techniques for Sub-100nm Trench DRAMs", IEEE, 4 pages, (2001).
<u>IN</u>	SEIDL, H. et al., "A Fully Integrated Al ₂ O ₃ Trench Capacitor DRAM for Sub-100nm Technology", IEEE, 4 pages, (2002).

Examiner	<u>Dan Nagy</u>	Date Considered	11/13/06
*Examiner:	Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		
Form PTO 1449	Patent and Trademark Office - U.S. Department of Commerce		